

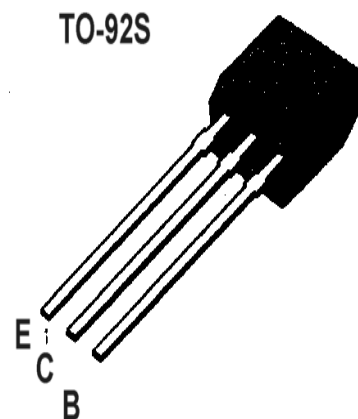
PNP Transistors

—PNP Silicon—

APPLICATION: General purpose applications.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.6	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	55~150	$^\circ\text{C}$


ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$, $R_G=10\Omega$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV_{CBO}	-60			V	$I_C=-0.1\text{mA}$	$I_E=0$	
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40			V	$I_C=-1\text{mA}$	$I_B=0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E=-0.1\text{mA}$	$I_C=0$	
Collector Cut-off Current	I_{CBO}			-0.1	μA	$V_{CB}=-50\text{V}$	$I_E=0$	
Emitter Cut-off Current	I_{EBO}			-0.1	μA	$V_{EB}=-3\text{V}$	$I_C=0$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.3	V	$I_C=-0.5\text{A}$	$I_B=-50\text{mA}$	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	$I_C=-0.5\text{A}$	$I_B=-50\text{mA}$	
DC Current Gain	h_{FE}	100		300	β	$V_{CE}=-10\text{V}$	$I_C=-0.15\text{A}$	
Gain bandwidth product	f_T	200			MHz	$V_{CE}=-20\text{V}$	$I_E=-50\text{mA}$	$f=100\text{MHz}$
Common Base Output Capacitance	C_{ob}			8	pF	$V_{CB}=-10\text{V}$	$I_E=0$	$f=1\text{MHz}$
Turn on Time	t_{on}			45	ns	$V_{cc}=-30\text{V}$	$I_c=-0.15\text{A}$	$I_{B1}=-15\text{mA}$
Turn off Time	t_{off}			100	ns	$V_{cc}=-30\text{V}$	$I_{B1,2}=-15\text{mA}$	$I_c=-0.15\text{A}$

 h_{FE} Classification And Marking

Print Mark 2N2907

Classification

 h_{FE} 100~300